

HD74HC283

4-bit Binary Full Adder

REJ03D0607-0200
 (Previous ADE-205-485)
 Rev.2.00
 Jan 31, 2006

Description

The sum (Σ) outputs are provided for each bit and the resultant carry (C_4) is obtained from the fourth bit. This adder features full internal look ahead across all four bits. This provides the system designer with partial look-ahead performance at the economy and reduced package count of a ripple-carry implementation. The adder logic, including the carry, is implemented in its true form meaning that the end-around carry can be accomplished without the need for logic or level inversion.

Features

- High Speed Operation: $t_{pd} = 19$ ns typ ($C_L = 50$ pF)
- High Output Current: Fanout of 10 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2$ to 6 V
- Low Input Current: 1 μ A max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max ($T_a = 25^\circ\text{C}$)
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74HC283P	DILP-16 pin	PRDP0016AE-B (DP-16FV)	P	—
HD74HC283FPEL	SOP-16 pin (JEITA)	PRSP0016DH-B (FP-16DAV)	FP	EL (2,000 pcs/reel)
HD74HC283RPEL	SOP-16 pin (JEDEC)	PRSP0016DG-A (FP-16DNV)	RP	EL (2,500 pcs/reel)

Note: Please consult the sales office for the above package availability.

Function Table

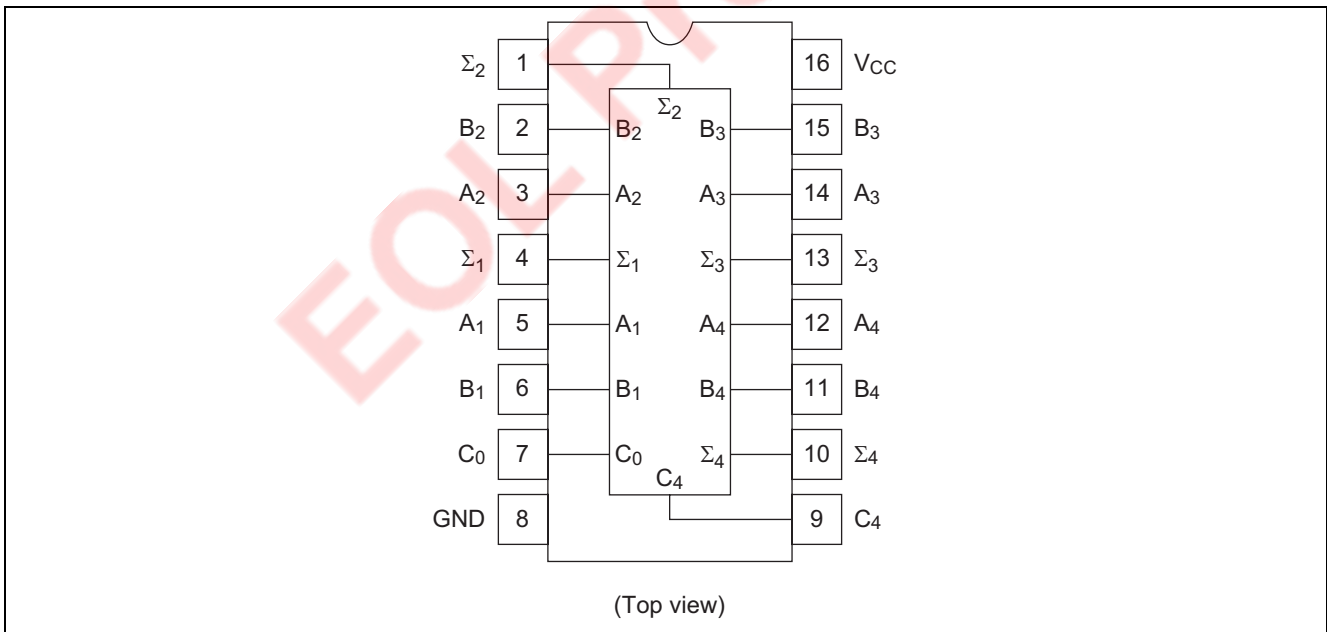
Inputs				Outputs					
				When C ₀ = L/When C ₂ = L			When C ₀ = H/When C ₂ = H		
A ₁ /A ₃	B ₁ /B ₃	A ₂ /A ₄	B ₂ /B ₄	Σ ₁ /Σ ₃	Σ ₂ /Σ ₄	C ₂ /C ₄	Σ ₁ /Σ ₃	Σ ₂ /Σ ₄	C ₂ /C ₄
L	L	L	L	L	L	L	H	L	L
H	L	L	L	H	L	L	L	H	L
L	H	L	L	H	L	L	L	H	L
H	H	L	L	L	H	L	H	H	L
L	L	H	L	L	H	L	H	H	L
H	L	H	L	H	H	L	L	L	H
L	H	H	L	H	H	L	L	L	H
H	H	H	L	L	L	H	H	L	H
L	L	L	H	L	H	L	H	H	L
H	L	L	H	H	H	L	L	L	H
L	H	L	H	H	H	L	L	L	H
H	H	L	H	L	L	H	H	L	H
L	L	H	H	L	L	H	H	L	H
H	L	H	H	H	L	H	L	H	H
L	H	H	H	H	L	H	L	H	H
H	H	H	H	L	H	H	H	H	H

H : high level

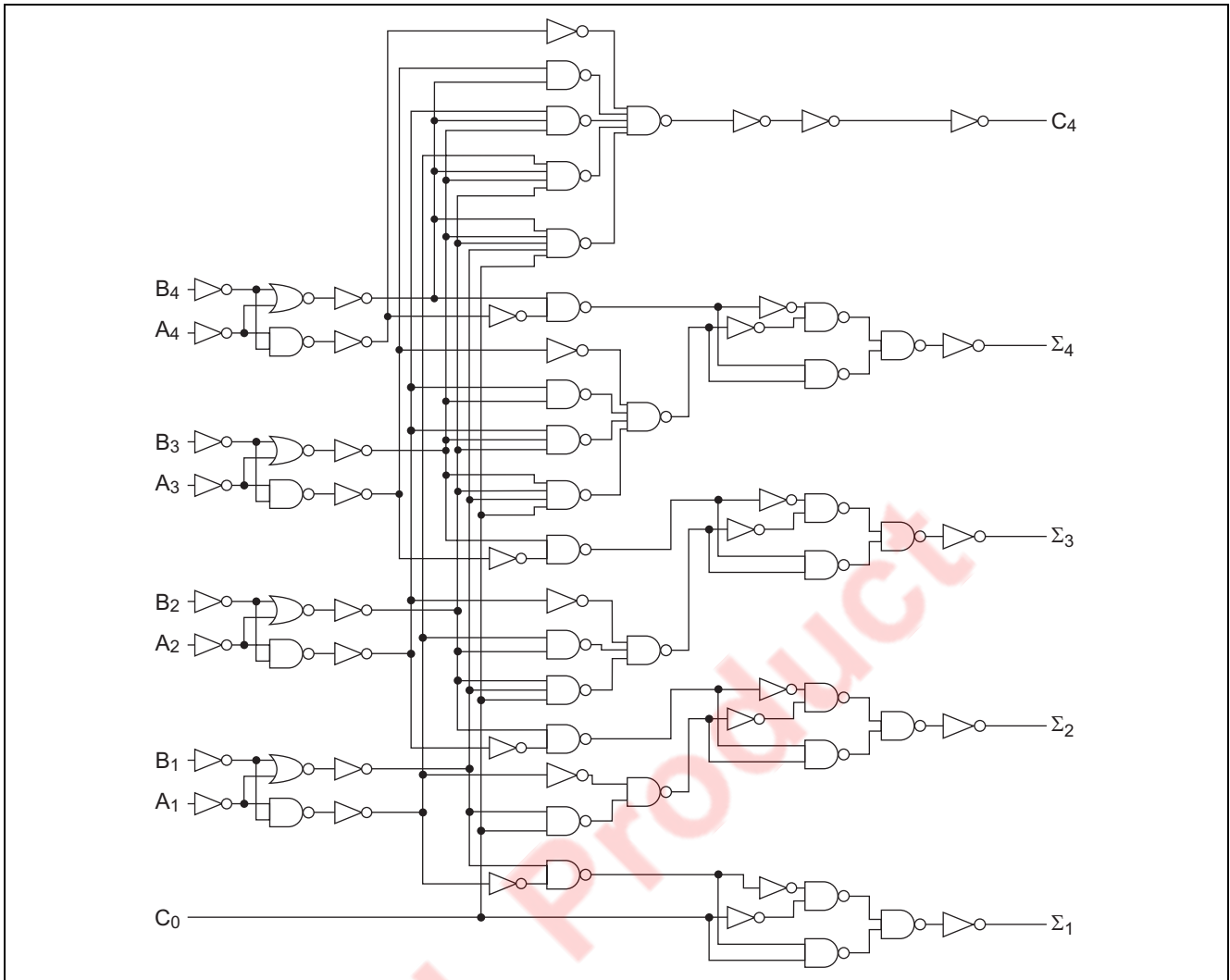
L : low level

Note: Input conditions at A₁, B₁, A₂, B₂, and C₀ are used to determine outputs Σ₁ and Σ₂ and the value of the internal carry C₂. The values at C₂, A₃, B₃, A₄ and B₄ are then used to determine outputs Σ₃, Σ₄ and C₄.

Pin Arrangement



Logic Diagram



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit
Supply voltage range	V_{CC}	-0.5 to 7.0	V
Input / Output voltage	V_{IN}, V_{OUT}	-0.5 to $V_{CC} + 0.5$	V
Input / Output diode current	I_{IK}, I_{OK}	± 20	mA
Output current	I_O	± 25	mA
V_{CC}, GND current	I_{CC} or I_{GND}	± 50	mA
Power dissipation	P_T	500	mW
Storage temperature	T_{stg}	-65 to +150	$^{\circ}C$

Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V_{CC}	2 to 6	V	
Input / Output voltage	V_{IN}, V_{OUT}	0 to V_{CC}	V	
Operating temperature	T_a	-40 to 85	°C	
Input rise / fall time ^{*1}	t_r, t_f	0 to 1000	ns	$V_{CC} = 2.0\text{ V}$
		0 to 500		$V_{CC} = 4.5\text{ V}$
		0 to 400		$V_{CC} = 6.0\text{ V}$

Notes: 1. This item guarantees maximum limit when one input switches.
 Waveform: Refer to test circuit of switching characteristics.

Electrical Characteristics

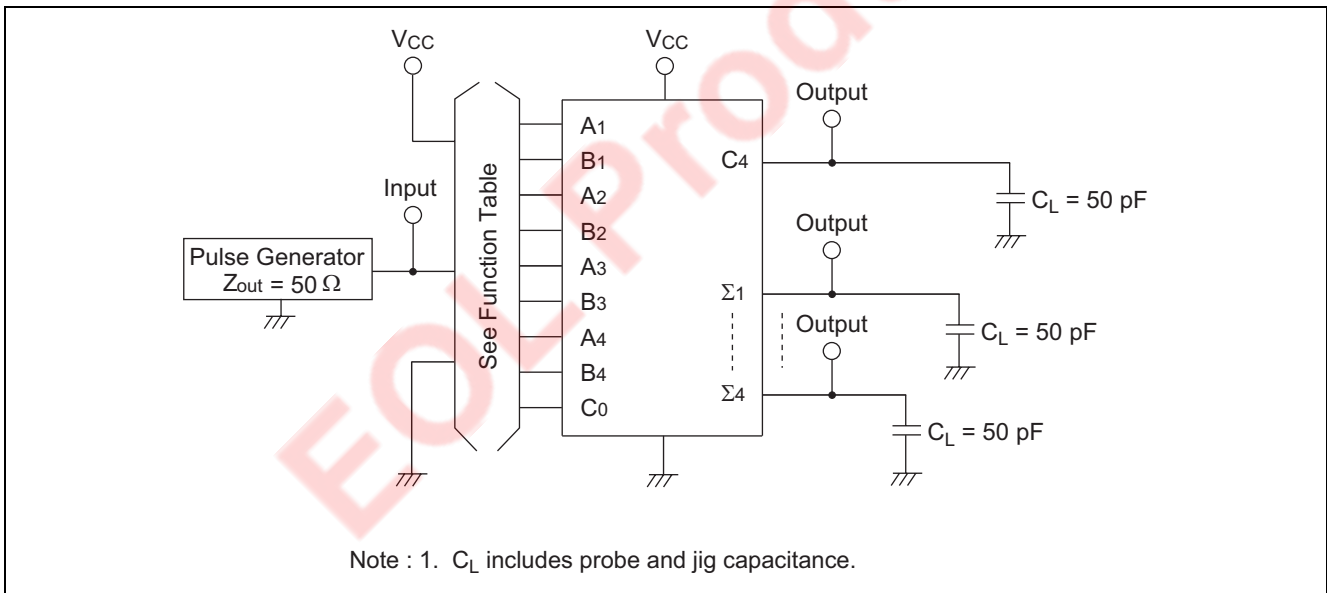
Item	Symbol	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40\text{ to }+85^\circ\text{C}$		Unit	Test Conditions	
			Min	Typ	Max	Min	Max			
Input voltage	V_{IH}	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V_{IL}	2.0	—	—	0.5	—	0.5	V		
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V_{OH}	2.0	1.9	2.0	—	1.9	—	V	$V_{in} = V_{IH}\text{ or }V_{IL}$	$I_{OH} = -20\ \mu\text{A}$
		4.5	4.4	4.5	—	4.4	—			$I_{OH} = -4\ \text{mA}$
		6.0	5.9	6.0	—	5.9	—			$I_{OH} = -5.2\ \text{mA}$
		4.5	4.18	—	—	4.13	—			
		6.0	5.68	—	—	5.63	—			
	V_{OL}	2.0	—	0.0	0.1	—	0.1	V	$V_{in} = V_{IH}\text{ or }V_{IL}$	$I_{OL} = 20\ \mu\text{A}$
		4.5	—	0.0	0.1	—	0.1			
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33			$I_{OL} = 4\ \text{mA}$
		6.0	—	—	0.26	—	0.33			$I_{OL} = 5.2\ \text{mA}$
Input current	I_{in}	6.0	—	—	± 0.1	—	± 1.0	μA	$V_{in} = V_{CC}\text{ or GND}$	
Quiescent supply current	I_{CC}	6.0	—	—	4.0	—	40	μA	$V_{in} = V_{CC}\text{ or GND}, I_{out} = 0\ \mu\text{A}$	

Switching Characteristics

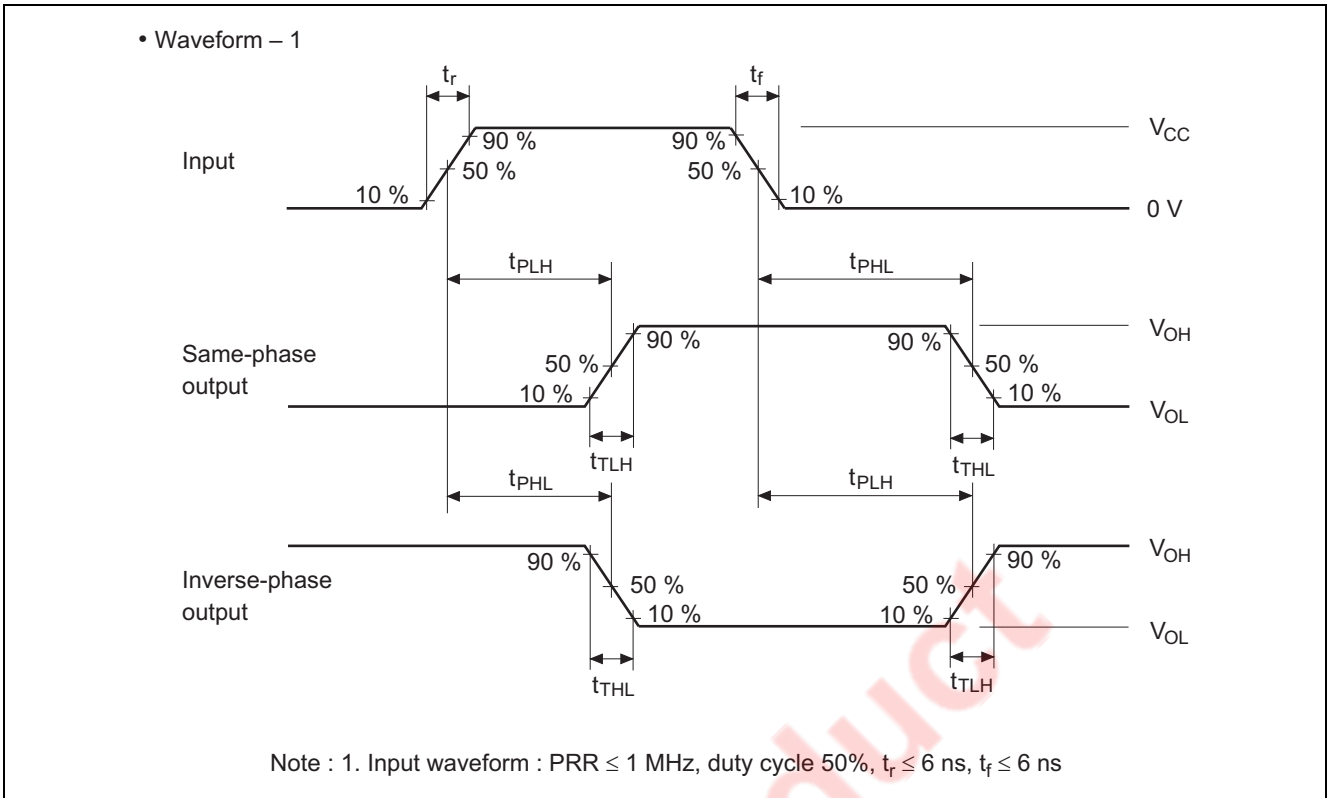
($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

Item	Symbol	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40 \text{ to } +85^\circ\text{C}$		Unit	Test Conditions
			Min	Typ	Max	Min	Max		
Propagation delay time	t_{PLH}	2.0	—	—	150	—	190	ns	C_0 to Σ_1
		4.5	—	19	30	—	38		
		6.0	—	—	26	—	33		
	t_{PHL}	2.0	—	—	150	—	190	ns	A_1 or B_1 to Σ_1
		4.5	—	19	30	—	38		
		6.0	—	—	26	—	33		
	t_{PLH}	2.0	—	—	150	—	190	ns	C_0 to C_4
		4.5	—	19	30	—	38		
		6.0	—	—	26	—	33		
	t_{PHL}	2.0	—	—	150	—	190	ns	A_1 or B_1 to C_4
		4.5	—	19	30	—	38		
		6.0	—	—	26	—	33		
Output rise/fall time	t_{TLH}	2.0	—	—	75	—	95	ns	
		4.5	—	5	15	—	19		
		6.0	—	—	13	—	16		
Input capacitance	C_{in}	—	—	5	10	—	10	pF	

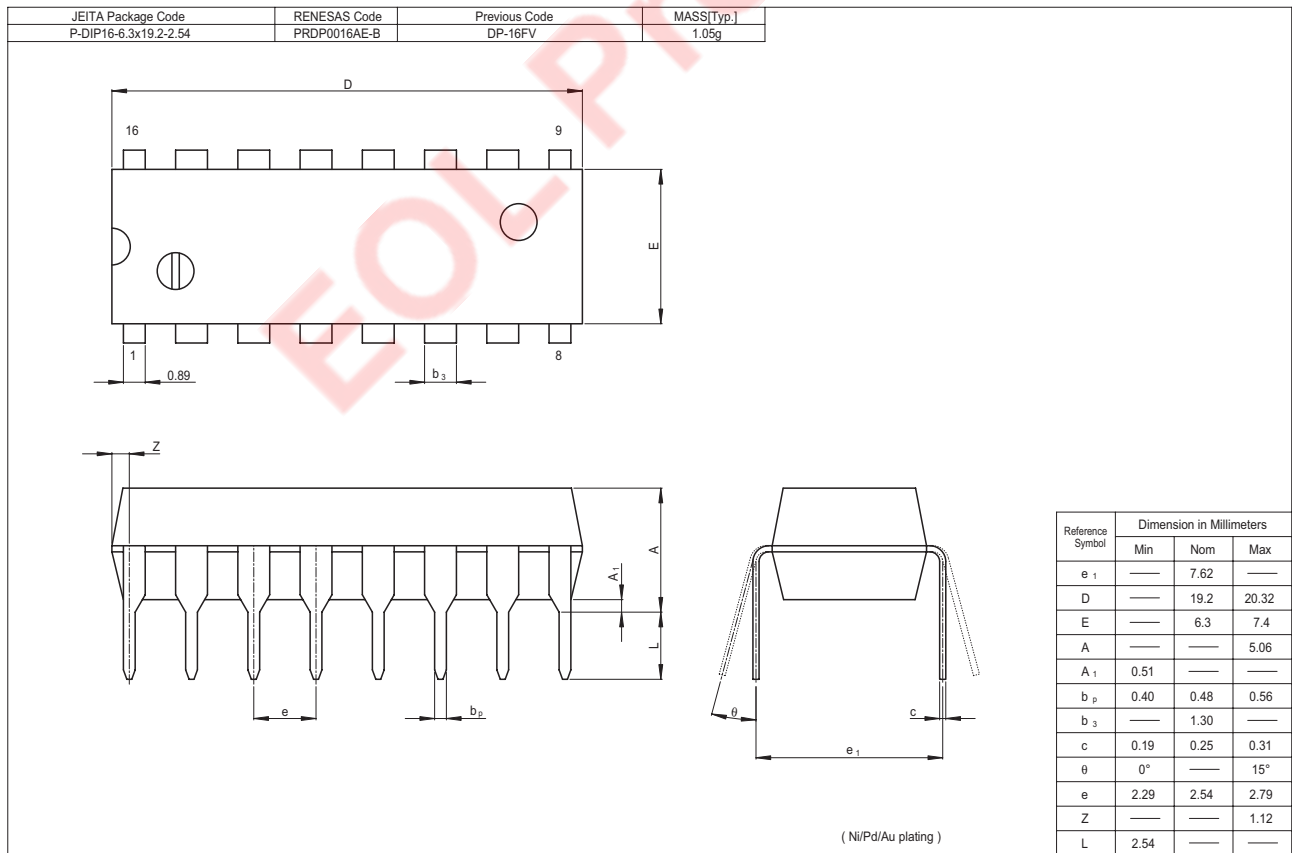
Test Circuit



Waveforms

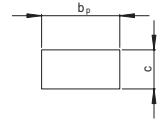
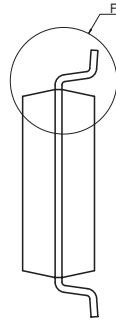
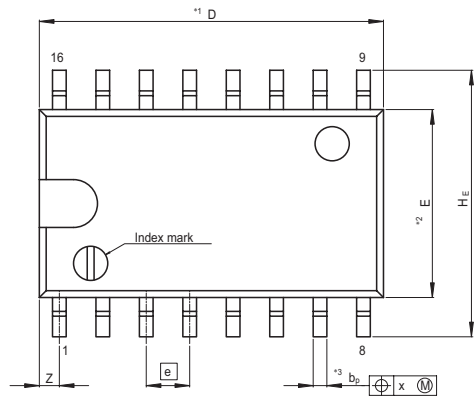


Package Dimensions

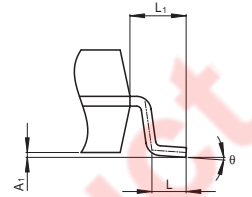
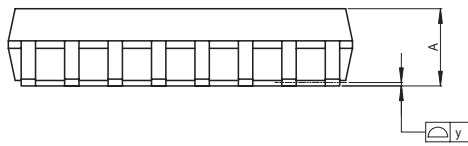


HD74HC283

JEITA Package Code P-SOP16-5.5x10.06-1.27	RENESAS Code PRSP0016DH-B	Previous Code FP-16DAV	MASS[Typ.] 0.24g
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Terminal cross section
(Ni/Pd/Au plating)

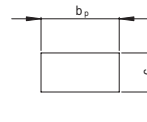
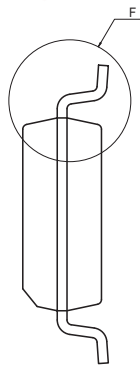
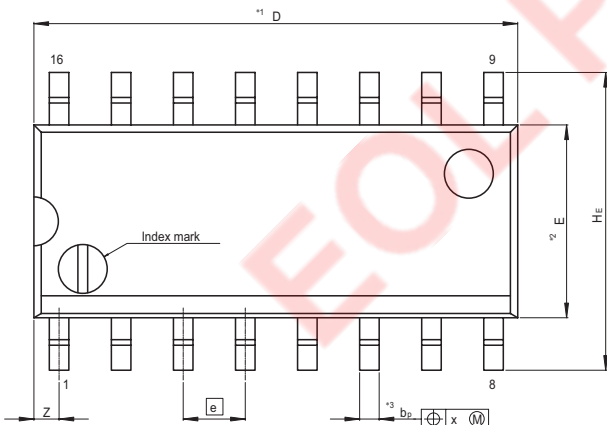


Detail F

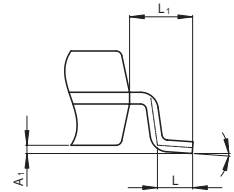
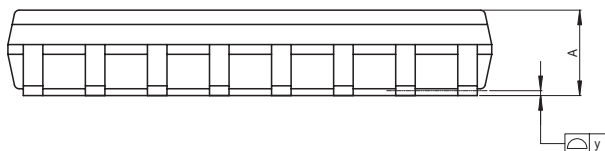
NOTE)
1. DIMENSIONS*1 (Nom)*AND*2*
DO NOT INCLUDE MOLD FLASH.
2. DIMENSION*3*DOES NOT
INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	—	10.06	10.5
E	—	5.50	—
A ₂	—	—	—
A ₁	0.00	0.10	0.20
A	—	—	2.20
b _p	0.34	0.40	0.46
b ₁	—	—	—
c	0.15	0.20	0.25
c ₁	—	—	—
θ	0°	—	8°
H _E	7.50	7.80	8.00
e	—	1.27	—
x	—	—	0.12
y	—	—	0.15
Z	—	—	0.80
L	0.50	0.70	0.90
L ₁	—	1.15	—

JEITA Package Code P-SOP16-3.95x9.9-1.27	RENESAS Code PRSP0016DG-A	Previous Code FP-16DNV	MASS[Typ.] 0.15g
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Terminal cross section
(Ni/Pd/Au plating)



Detail F

NOTE)
1. DIMENSIONS*1 (Nom)*AND*2*
DO NOT INCLUDE MOLD FLASH.
2. DIMENSION*3*DOES NOT
INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	—	9.90	10.30
E	—	3.95	—
A ₂	—	—	—
A ₁	0.10	0.14	0.25
A	—	—	1.75
b _p	0.34	0.40	0.46
b ₁	—	—	—
c	0.15	0.20	0.25
c ₁	—	—	—
θ	0°	—	8°
H _E	5.80	6.10	6.20
e	—	1.27	—
x	—	—	0.25
y	—	—	0.15
Z	—	—	0.635
L	0.40	0.60	1.27
L ₁	—	1.08	—

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